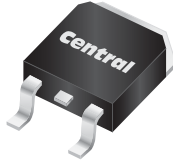


CSDD-8M
CSDD-8N

**SURFACE MOUNT
SILICON CONTROLLED RECTIFIERS
8.0 AMP, 600 THRU 800 VOLT**



D²PAK CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CSDD-8M series type is an Epoxy Molded Silicon Controlled Rectifier designed for sensing circuit applications and control systems.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)	SYMBOL	CSDD-8M	CSDD-8N	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	600	800	V
RMS On-State Current ($T_C=90^\circ\text{C}$)	$I_{T(RMS)}$		8.0	A
Peak One Cycle Surge, $t=10\text{ms}$	I_{TSM}		70	A
I^2t Value for Fusing, $t=10\text{ms}$	I^2t		24	A ² s
Peak Gate Power, $t_p=10\mu\text{s}$	P_{GM}		40	W
Average Gate Power Dissipation	$P_{G(AV)}$		1.0	W
Peak Forward Gate Current, $t_p=10\mu\text{s}$	I_{FGM}		4.0	A
Peak Forward Gate Voltage, $t_p=10\mu\text{s}$	V_{FGM}		16	V
Peak Reverse Gate Voltage, $t_p=10\mu\text{s}$	V_{RGM}		5.0	V
Critical Rate of Rise of On-State Current	di/dt		50	A/ μs
Operating Junction Temperature	T_J	-40 to +125		$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +150		$^\circ\text{C}$
Thermal Resistance	θ_{JA}	60		$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	2.5		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated V_{DRM}, V_{RRM}			10	μA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$			2.0	mA
I_{GT}	$V_D=12\text{V}, R_L=10\Omega$		3.0	15	mA
I_H	$I_T=100\text{mA}$		7.3	20	mA
V_{GT}	$V_D=12\text{V}, R_L=10\Omega$		0.9	1.5	V
V_{TM}	$I_{TM}=16\text{A}, t_p=380\mu\text{s}$		1.3	1.8	V
dv/dt	$V_D=2/3 V_{DRM}, T_C=125^\circ\text{C}$	200			V/ μs

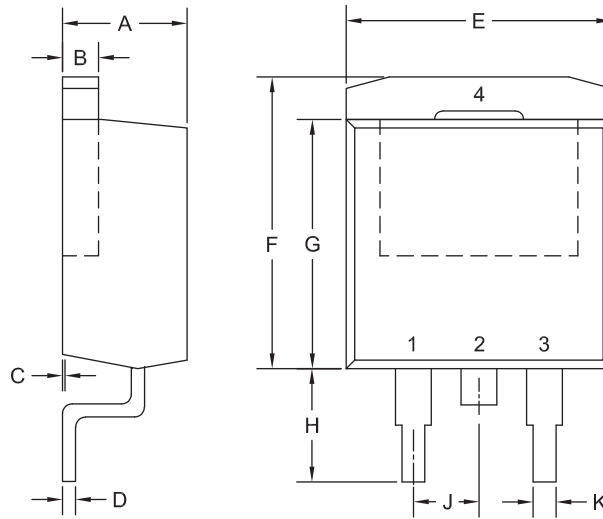
R3 (11-January 2018)

CSDD-8M
CSDD-8N

SURFACE MOUNT
SILICON CONTROLLED RECTIFIERS
8.0 AMP, 600 THRU 800 VOLT



D²PAK CASE - MECHANICAL OUTLINE



R3

LEAD CODE:

- 1) Cathode
- 2) Anode
- 3) Gate
- 4) Anode

MARKING:

FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.163	0.189	4.14	4.80
B	0.045	0.055	1.14	1.40
C	0.000	0.010	0.00	0.25
D	0.012	0.028	0.30	0.70
E	0.386	0.415	9.80	10.55
F	0.378	0.417	9.60	10.60
G	0.335	0.358	8.50	9.10
H	0.188	0.236	4.78	6.00
J	0.093	0.108	2.35	2.75
K	0.030	0.035	0.75	0.90

D2PAK (REV: R3)

R3 (11-January 2018)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: www.centrasemi.com/terms